



15.14/5048

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: FURUHATA et al.)
Serial No.: 09/604,702)
Filed: June 23, 2000)
For: SEMICONDUCTOR DEVICES HAVING A)
NON-VOLATILE MEMORY TRANSISTOR)

Group Art Unit: 2812

Examiner: Booth, R.

AMENDMENT

#13/B
4-1-03
Payton

Box RCE
Commissioner for Patents
Washington, D.C. 20231

Dear Sirs:

Applicant filed a Notice of Appeal in response to the Office Action dated August 13, 2002. The Notice of Appeal was mailed to the Office on Jan. 14, 2002 and was apparently entered by the Office on Jan. 21, 2003. Applicant has filed an Request for Continued Examination together with this Amendment. Applicant respectfully requests entry and consideration of the following:

IN THE SPECIFICATION:

Please delete the paragraph at page 1, lines 6-13 and replace it with the following:

B1
--U.S. Patent No. 6,429,073 is hereby incorporated by reference in its entirety. U.S. Patent No. 6,522,587 is hereby incorporated by reference in its entirety. Japanese patent application no. 11-177146, filed June 23, 1999, is hereby incorporated by reference in its entirety.--

IN THE CLAIMS:

Please amend claims 1-2, 4, 6-10, 12, 19, 22, 24, 26-27, and 29 as follows:

B2
1. (amended) A semiconductor device comprising a memory region, first, second and third transistor regions including field effect transistors that operate at different voltage levels,

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TECHNICAL STAFF